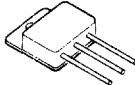
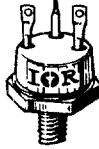


Power MOSFETS High Reliability

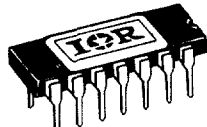
TO-258 — N-Channel

Part Number	V _{DS} Drain Source Voltage (Volts)	R _{DS(on)} On-State Resistance (Ohms)	I _D Continuous Drain Current 25° Case (Amps)	I _{DM} Pulse Drain Current (Amps)	P _D Max Power Dissipation (Watts)	Case Outline Number (5)	Notes	Case Style
IRFV360 IRFV460	400 500	0.21 0.27	22 21	80 70	250	H20	(4)	TO-258 

TO-61 — N-Channel



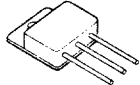
Part Number	V _{DS} Drain Source Voltage (Volts)	R _{DS(on)} On-State Resistance (Ohms)	I _D Continuous Drain Current 25° Case (Amps)	I _{DM} Pulse Drain Current (Amps)	P _D Max Power Dissipation (Watts)	Case Outline Number (5)	Notes	Case Style
IRFH150 IRFH250 IRFH350 IRFH450	100 200 400 500	0.06 0.09 0.3 0.4	30 30 15 13	120 120 56 52	150	H14	(4)	TO-210AC TO-61 

Side Braze Ceramic — N-Channel

Part Number	V _{DS} Drain Source Voltage (Volts)	R _{DS(on)} On-State Resistance (Ohms)	I _D Continuous Drain Current 25° Case (Amps)	I _{DM} Pulse Drain Current (Amps)	P _D Max Power Dissipation (Watts)	Case Outline Number (5)	Notes	Case Style
IRFG120 IRFG110	100	3.0 0.8	0.45 0.95	1.6 4	1 1.4	H15		MO-036AB 
P-Channel								
IRFG9110	-100	1.4	-0.75	-3	1.4			
N & P Channel								
IRFG5110 IRFG6110	100 -100 100 -100	0.8 0.8 0.8 1.4	1 -0.95 0.95 -0.95	4 -4 4 -3.5	1.4			

Schottky Rectifier

High Reliability

Part Number	V _{RRM} (V)	I _{F(AV)} @ T _c		V _{FM} @ I _{FM} T _j = 100°C I _{FM} = I _{F(AV)} (V)	I _{FSM} (1)		I _{RM} @ T _j = 125°C & Rated V _{RRM} (mA)	Max. T _j (°C)	Outline Number (5)	Notes	Case Style					
		(A)	(°C)		50Hz (A)	60Hz (A)										
15CGQ100 20GQ100 22CGQ045 22DGQ045 25GQ045	100 100 45 45 45	15.0 20.0 22.0 22.0 22.0	100	0.77 0.92 0.89 0.89 0.85	TBD	TBD	7 45 20 20 45	150 175 175 175 175	H19	(2) (3)	TO-254AA M-PAK (4) 					
15CLQ100 20CLQ045	100 45	15.0 20.0		0.80 0.75			228 285	240 300				15 15	175 175	H21	(2)	SMD-1 
45CKQ100 60CKQ045	100 45	45.0 60.0		TBD			TBD	TBD				TBD	175 175	H20	(2) (4)	TO-258 

(1) PEAK HALF-CYCLE SINE WAVE, FOLLOWING ANY RATED LOAD CONDITION, V_{RRM} REAPPLIED.

(2) DUAL-DIE COMMON CATHODE CONFIGURATION

(3) DUAL-DIE DOUBLER CONFIGURATION.

(4) PACKAGES CONTAINING BERYLLIA SHALL NOT BE GROUND, SANDBLASTED, MACHINED, OR HAVE OTHER OPERATIONS PERFORMED ON THEM WHICH WILL PRODUCE BERYLLIA OR BERYLLIUM DUST. FURTHERMORE, BERYLLIUM OXIDE PACKAGES SHALL NOT BE PLACED IN ACIDS THAT WILL PRODUCE FUMES CONTAINING BERYLLIUM.

(5) FOR CASE OUTLINE DRAWING SEE PAGE 136.